

**Moscow State Institute of Electronic Technology
(Technical University)**
Zelenograd, Russia

Centre «Nanotechnologies in electronics»

Reporter: Stas.V. Khartov

**Probe technology applications
and molecule-based devices**

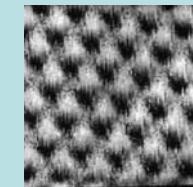


THE BRIEF PLAN

- Historic background of the centre «Nanotechnologies in electronics», MIET
 - Activities of the centre in the probe nanotechnology:
 - ✓ Probes and methods of their producing
 - ✓ Objects visualization
 - ✓ Objects manipulation
 - ✓ Force Lithography
 - ✓ Local anodic oxidation (LAO)
 - ✓ Molecular conductors in polymeric matrix
 - & Conductive NT/polymer nanocomposites

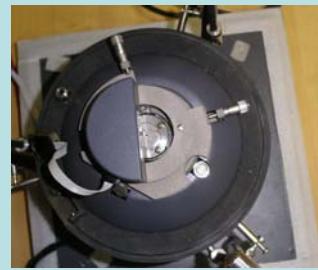
The Centre «Nanotechnologies in electronics», MIET

The first in Russia technological scanning tunneling microscope (1987)



Atomic resolution of HOPG surface

For the present moment the center has :



- Scanning probe microscope (SPM) for carrying out of precision lithograph (Solver Pro, NT-MDT)
- 3 universal SPM (NT-MDT)
- 5 scientific training SPM (Nanoeducator, NT-MDT)
- 2 scanning tunneling home-made microscopes (TTM)
- Equipment of molecular conductors formation



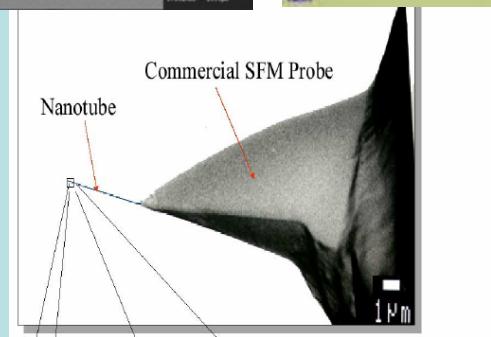
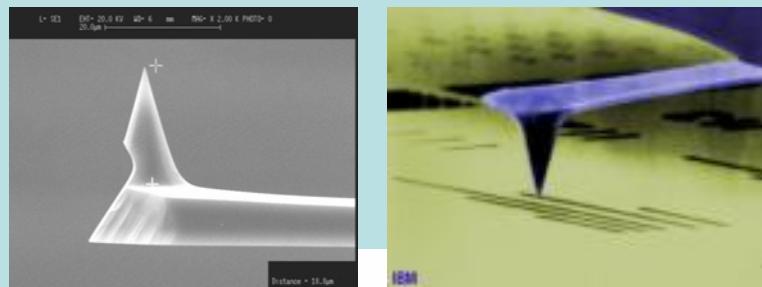
Installation of the first in the center ultra high vacuum SPM in structure of nanotechnology facility NANOFAB 100 (NT-MDT) with FIB and MLE blocks is planned.



NANOFAB 100 includes the three ultra high vacuum (10-11 Torr) chambers – analytical, loading and chamber of replaceable probe sensor assemblies

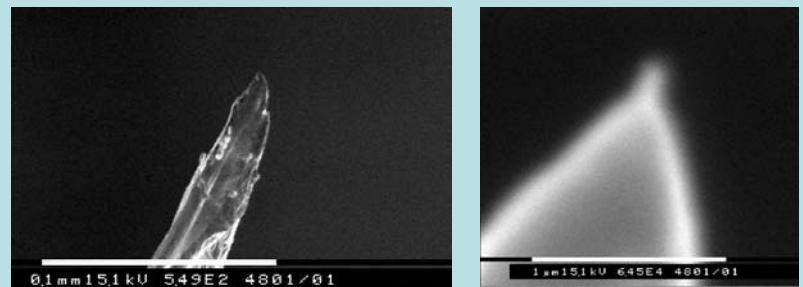
Probes and methods of their producing

Atomic force microscope (AFM) probes



The basic material is Si;
The typical curvature radius is on the order of 10 nm; For aspect ratio increase the NT-based probes are applied

Scanning tunneling microscope (STM) probes



SEM image of Pt/Ir - probe (MIET, 2005)

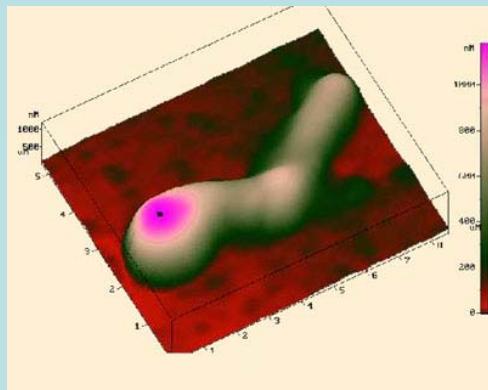
SEM image of W-probe (MIET, 2005)

Pt/Ir-probes are free from surface oxides and posts in manufacturing. The main method for preparing is mechanical cutting of Pt/Ir wire

W-probes are prepared by electrochemical method. The typical curvature radius in our case is on the order of 15 nm and the aspect ratio is on a level of 30°

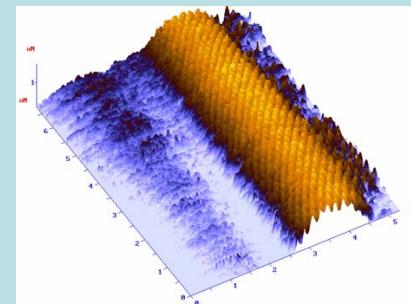
Primary application - objects visualization

Images of objects on insulating substrates

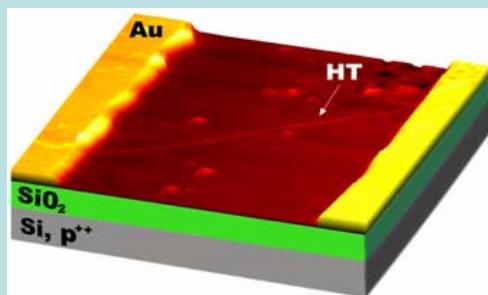


AFM image of
Bacterium Corynobacterium diphtheriae on glass substrate (MIET, 2002)

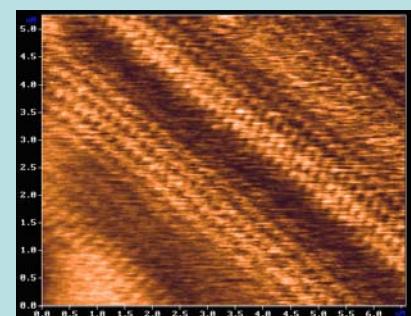
Atomic resolution of carbon nanotubes in ambient conditions



STM image of carbon nanotube (NT) (MIET, 2003)



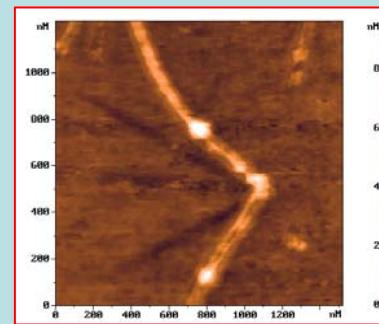
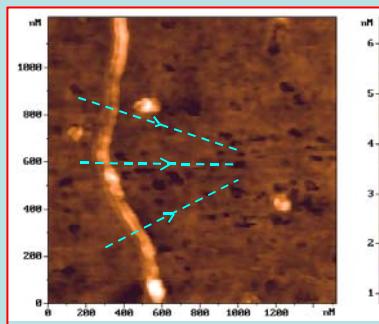
AFM image of NT between conducting paths (MIET, 2004)



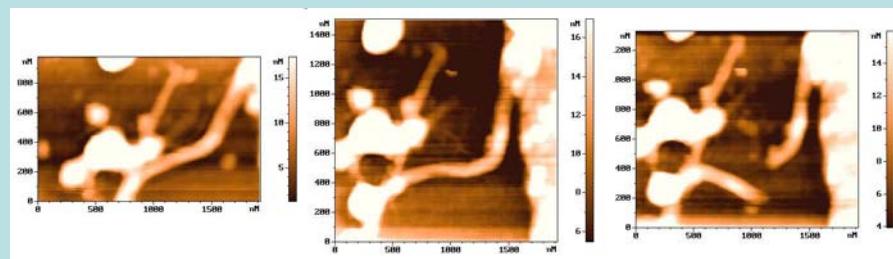
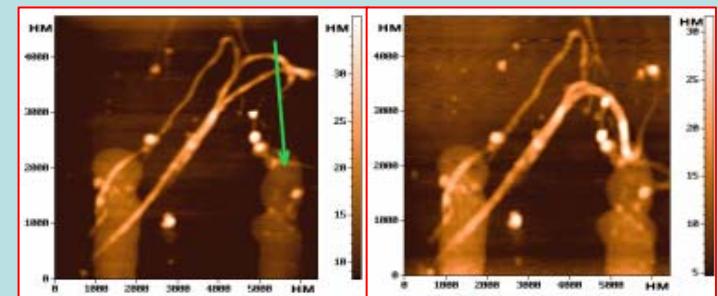
STM image of CNT bundle (MIET, 2003)

Micro and nanoobjects manipulation

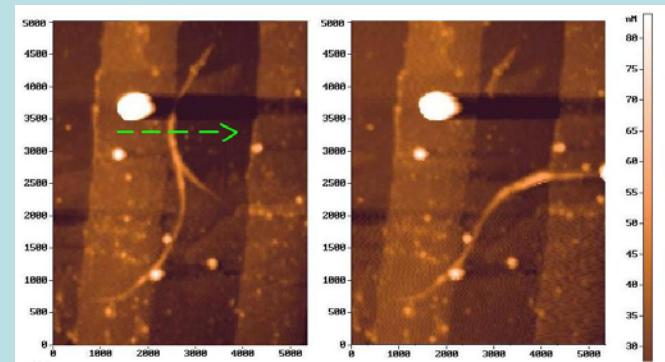
NT bending and rupture



NT movement for formation of electric contact with path



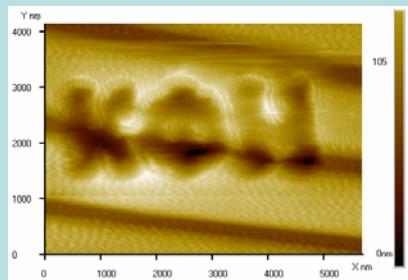
AFM images
(MIET, 2003-2005)



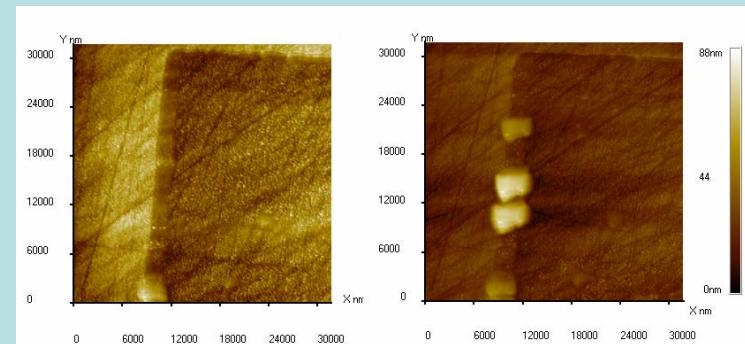
AFM images
(MIET, 2003- 2006)

Force Lithography

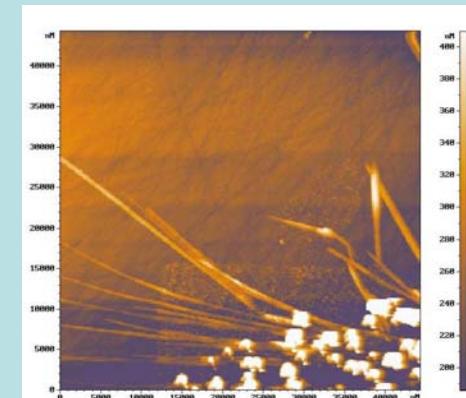
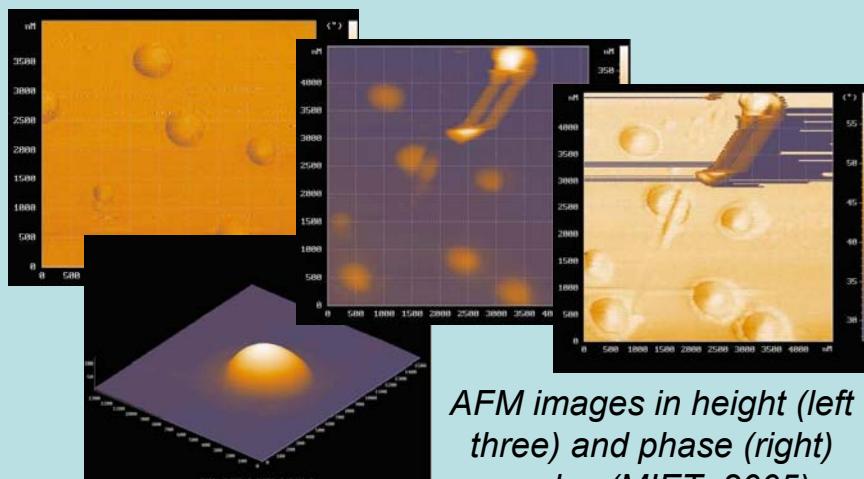
Lithography on polymer (performed on SPM «NanoEducator»)



Creation of the centers of NT growth on a film of catalyst (performed on SPM «NanoEducator»)

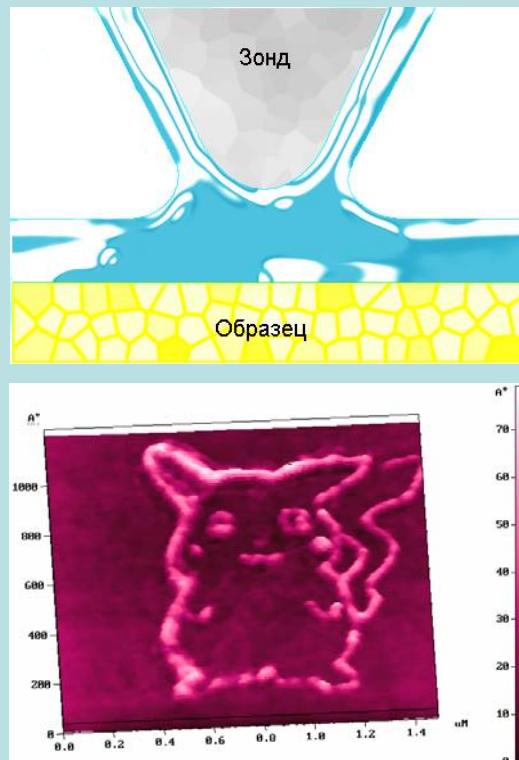


Breaking up of one of the knobs shows the viscous state of knobs' inside



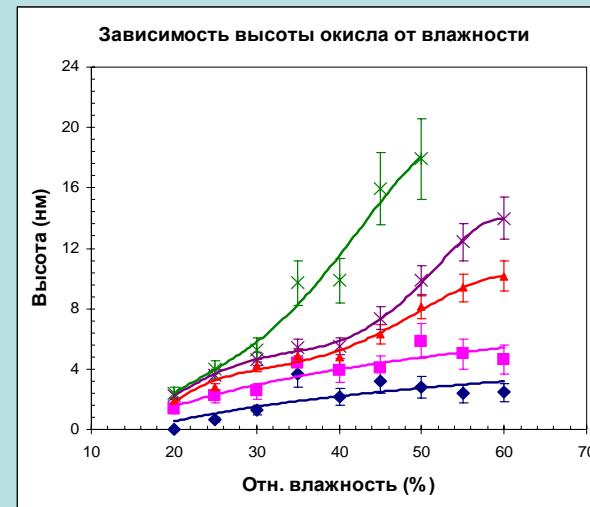
Local anodic oxidation (LAO)

Model of system
“probe – quasiliquid –substrate”



AFM image of LAO formed pattern
(MIET, 2003)

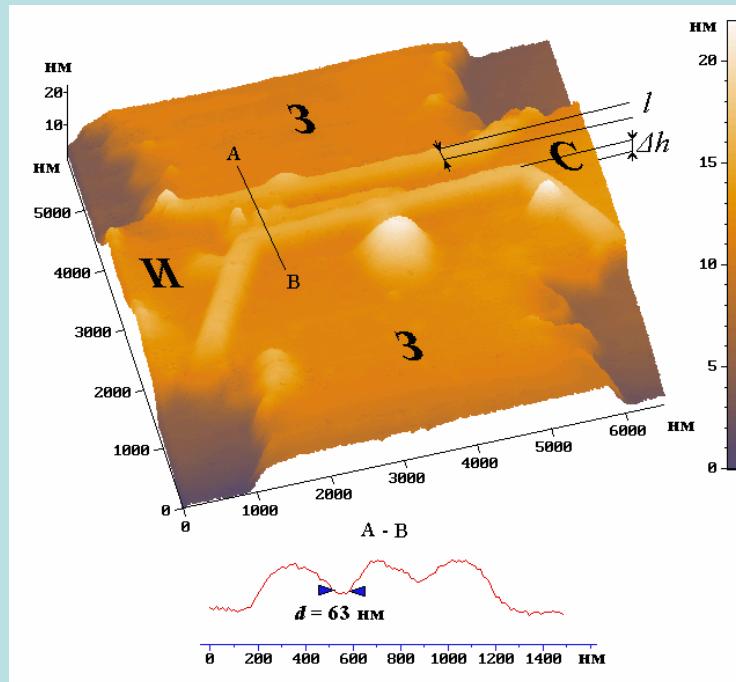
Dependence of oxide height from humidity for
Al on Si



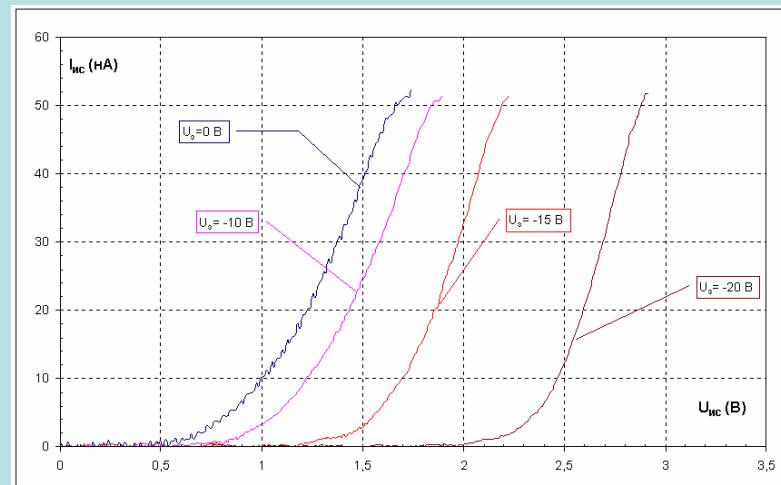
Bottom-up: voltage magnitude –
4 V, 4.5 V, 5 V, 5.5 V u 6 V.
(MIET, 2004)

The natural air adsorbate plays the important role in LAO, since it is a source of ions of oxygen

Quasione-dimensional conductor on the basis of tantalic film in an external cross-section field



Topography of quasione-dimensional channel formed by LAO oxidation of tantalic cross : l –width, Δh –height of oxide over tantalic surface, d – visual width of AFM image of channel

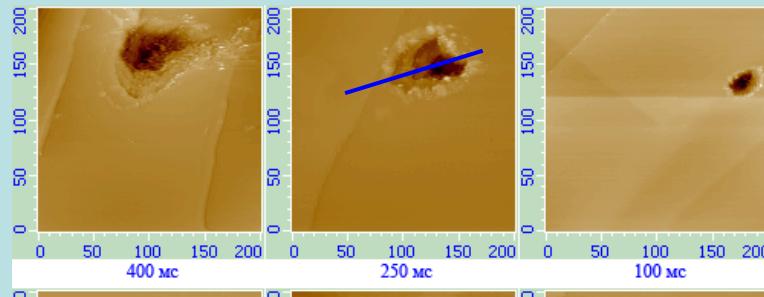


AFM image of structure obtained by LAO (MIET, 2004)

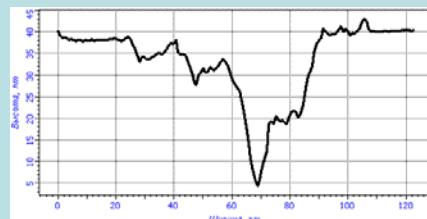
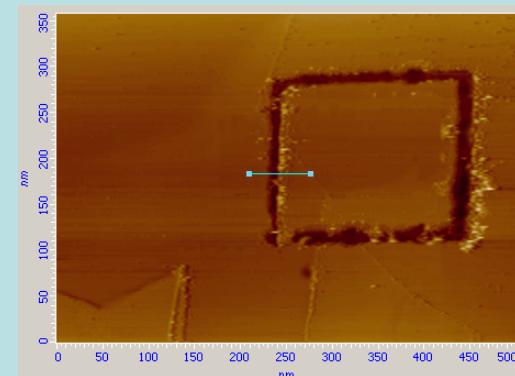
Static current-voltage characteristic of quasione-dimensional channel with visual width $d < 60$ nm (MIET, 2004)

Local anodic oxidation of HOPG in tunneling mode

HOPG surface topography after LAO with voltage 3.6 V and duration of impulse 20, 40, 70, 100, 250, 400 ms correspondingly



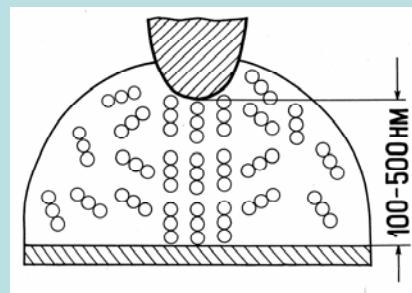
Graphite sheets represent the highly ordered 2D structures with ballistic electron transport and have volatile oxide



*STM images of modified HOPG surfaces (up) and cross section of the cracks (bottom)
(MIET, 2005)*

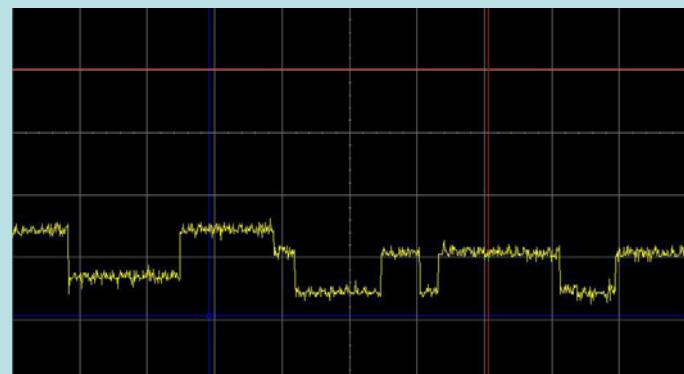
Molecular conductor between probe and substrate in polymeric matrix

Equivalent conductivity on 20 orders exceeds the conductivity of initial polymeric matrix and matches the silver



← *The scheme and view of the structure with molecular channel*

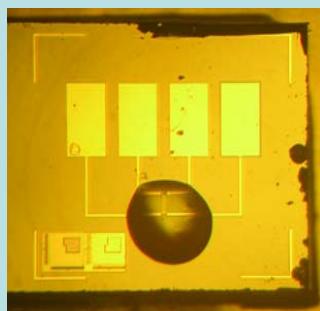
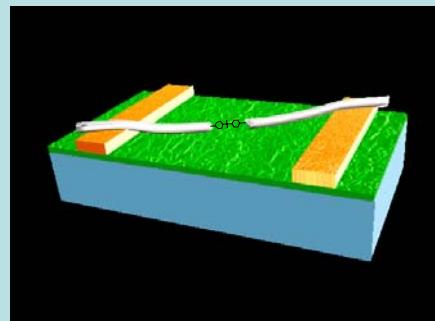
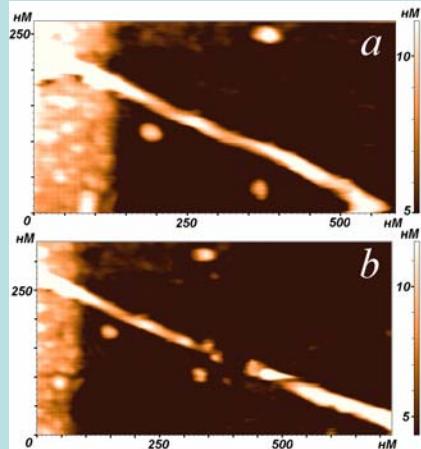
Heating of the hardened matrix leads to its volumetric expansion which causes the series of spontaneous step switchings of resistance of the structure. The steps are aliquot from **13 KOhm** – the quantum of ballistic resistance.



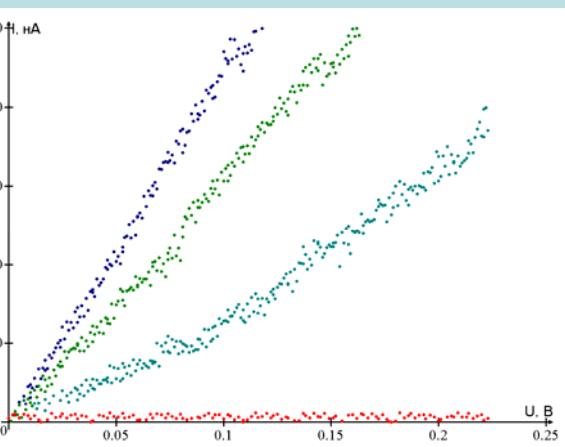
Oscillogram of signal from the structure, 10 mV and 1 ms per division (MIET, 2005)

Planar molecular conductor in polymeric matrix

The multiwalled carbon nanotubes play the role of electrodes and provide the required configuration of electric fields for molecular channel formation in the gap



The model and top view of the structure with NT and molecular channel



The modulation and switching of conductivity of molecular channel (MIET, 2005)

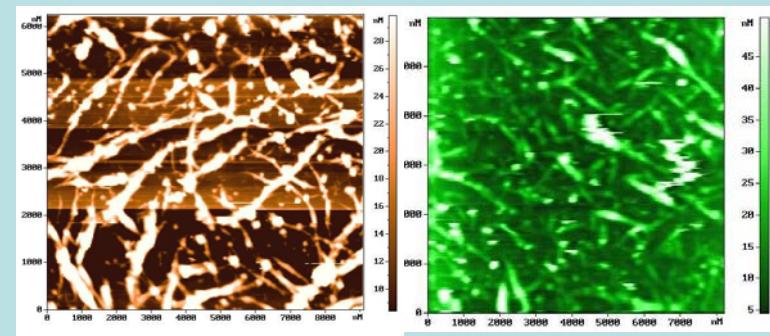
Conductive NT/epoxy nanocomposites

Nanotubes dispersed in polymer matrix acts as a system of electrodes for molecular channels

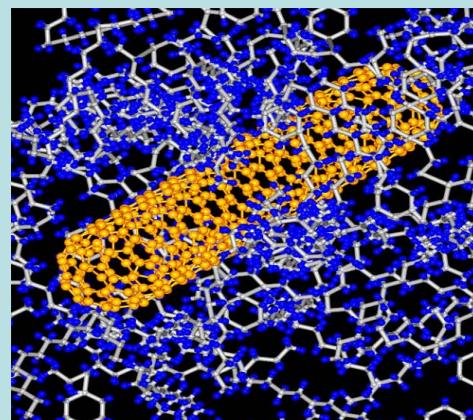


View of hardened NT/epoxy composite tablet with anisotropic conductivity (MIET, 2005)

Thin film composites are made on the base of NT nets



AFM images of NT nets with less (left) and more (right) densities (MIET, 2005)



← *Model of nanotube in polymeric matrix*



Questions?